

Claims 2, 3, 23 and 28 are canceled.

Claims 1, 15, 22, 27 and 29 are rewritten.

sub c1
A10

1. (Amended) A semiconductor assembly comprising:

a support structure having a top surface, wherein said support structure is a film; and

at least one semiconductor die having a top and bottom surface, said bottom surface having a smaller area than said top surface of said support structure, said at least one semiconductor die being secured at its bottom surface to said top surface of said support structure by a flowable adhesive material which does not extend past a perimeter of said at least one semiconductor die.

sub c2
A11

15. (Amended) A semiconductor assembly comprising:

a first semiconductor die having a top and a bottom surface;

a second semiconductor die having a top and bottom surface, said bottom surface having a smaller area than said top surface of said first semiconductor die, said second die being secured at its bottom surface to said top surface of said first semiconductor die by a flowable adhesive material which does not extend past a perimeter of said second semiconductor die; and

wherein said top surface of said first semiconductor die has at least one

A11
Cancelled

electrical contact area positioned at a location exterior to said perimeter of said second semiconductor die, and wherein a distance between said electrical contact area and said perimeter of said second semiconductor die is less than or equal to about 428 microns.

A12

22. (Amended) A semiconductor assembly comprising:

a first semiconductor die having a top and a bottom surface;

a support structure to which said bottom surface of said first semiconductor die is secured, wherein said support structure is a film;

a second semiconductor die having a top and a bottom surface, said bottom surface having a smaller area than said top surface of said first semiconductor die; and

a third semiconductor die having a top and a bottom surface, said bottom surface having a smaller area than said top surface of said first semiconductor die, said second and third semiconductor dies being secured at their bottom surface to said top surface of said first semiconductor die by a flowable adhesive material which does not extend past a perimeter of said second semiconductor die or said third semiconductor die.

A13

27. (Amended) A semiconductor assembly comprising:

a support structure;

a first semiconductor die having a top and bottom surface, said bottom surface being secured to said support structure;

A13
1m
Added

a second semiconductor die having a top and bottom surface, said bottom surface having a smaller area than said top surface of said first semiconductor die, said second die being secured at its bottom surface to said top surface of said first semiconductor die by a flowable adhesive material which does not extend past a perimeter of said second die; and

wherein said top surface of said first semiconductor die has at least one electrical contact area positioned at a location exterior to said perimeter of said second semiconductor die, and wherein a distance between said electrical contact area and said perimeter of said second semiconductor die is less than or equal to about 428 microns.

A14

29. (Amended) The semiconductor assembly of claim 27, wherein a distance between an electrical contact area on said top surface of said first semiconductor die and said perimeter of said second semiconductor die is less than or equal to about 200 microns.